1. Record Nr. UNISALENTO991003851729707536

Titolo	Alberi di confine : archeologia silvana a sud di Lecce / a cura di Michele Mainardi
Pubbl/distr/stampa	Galatina : Editrice salentina, 2003
Descrizione fisica	64 p. : ill. ; 24 cm
Altri autori (Persone)	Mainardi, Michele
Disciplina	581.9
Soggetti	Alberi - Lecce (Territorio) Flora - Lecce (Territorio) Plants - Trees - Lecce - Italy
Lingua di pubblicazione	Italiano
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	In testa al front.: Regione Puglia, Assessorato Pubblica Istruzione, CRSEC Le/39, San Cesario di Lecce

2. Record Nr. UNINA9910299617403321

Autore	Erlbacher Tobias
Titolo	Lateral Power Transistors in Integrated Circuits / / by Tobias Erlbacher
Pubbl/distr/stampa	Cham : , : Springer International Publishing : , : Imprint : Springer, , 2014
ISBN	3-319-00500-6
Edizione	[1st ed. 2014.]
Descrizione fisica	1 online resource (235 p.)
Collana	Power Systems, , 1612-1287
Disciplina	620 621.317 621.3815
Soggetti	Electronic circuits Power electronics Circuits and Systems Power Electronics, Electrical Machines and Networks Electronic Circuits and Devices
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Introduction -- Literature Review -- Research Methods.
Sommario/riassunto	The book summarizes and compares recent advancements in the development of novel lateral power transistors (LDMOS devices) for integrated circuits in power electronic applications. In its first part, the book motivates the necessity for lateral power transistors by a top-down approach: First, it presents typical energy conversion applications in modern industrial, automotive and consumer electronics. Next, it introduces common circuit topologies suitable for these applications, and discusses the feasibility for monolithic integration. Finally, the combination of power and logic functionality on a single chip is motivated and the requirements and limitations for the power semiconductor devices are deduced. The second part describes the evolution of lateral power transistors over the past decades from the simple pin-type concept to double-acting RESURF topologies. It describes the principle of operation for these LDMOS devices and discusses limitations of lateral power devices. Moreover, figures-of-merit are presented which can be used to evaluate the performance of

the novel lateral power transistors described in this book with respect to the LDMOS devices. In the last part, [..] the fundamental physical concepts including charge compensation and trench gate topologies are discussed. Also, the status of research in LDMOS devices on silicon carbide is presented. Advantages and drawbacks for each of these integration approaches are summarized, and the feasibility with respect to power electronic applications is evaluated.